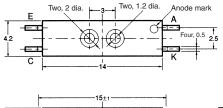
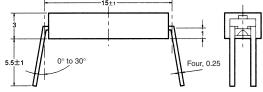
# **Photomicrosensor (Reflective)**

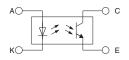
### ■ Dimensions

Note: All units are in millimeters unless otherwise indicated.





**Internal Circuit** 



Terminal No.	Name	
Α	Anode	
K	Cathode	
С	Collector	
E	Emitter	

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance	
3 mm max.	±0.3	
$3 < mm \le 6$	±0.375	
6 < mm ≤ 10	±0.45	
10 < mm ≤ 18	±0.55	
18 < mm ≤ 30	±0.65	

### ■ Features

- 3-mm-tall, thin model
- · RoHS Compliant.

## ■ Absolute Maximum Ratings (Ta = 25°C)

	Item	Symbol	Rated value
Emitter	Forward current	I <sub>F</sub>	50 mA (see note 1)
	Pulse forward current	I <sub>FP</sub>	1 A (see note 2)
	Reverse voltage	$V_R$	4 V
Detector	Collector–Emitter voltage	$V_{CEO}$	30 V
	Emitter–Collector voltage	$V_{\text{ECO}}$	
	Collector current	I <sub>C</sub>	20 mA
	Collector dissipation	$P_{C}$	100 mW (see note 1)
Ambient temperature	Operating	T <sub>opr</sub>	–40°C to 85°C
	Storage	T <sub>stg</sub>	–40°C to 85°C
Soldering ten	nperature	T <sub>sol</sub>	260°C (see note 3)

Note: 1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.

- 2. The pulse width is 10  $\mu s$  maximum with a frequency of 100 Hz.
- 3. Complete soldering within 10 seconds.

## **■** Ordering Information

Description	Model	
Photomicrosensor (reflective)	EE-SY171	

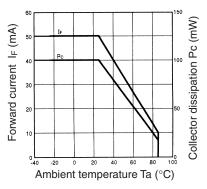
## ■ Electrical and Optical Characteristics (Ta = 25°C)

	Item	Symbol	Value	Condition
Emitter	Forward voltage	$V_{F}$	1.2 V typ., 1.5 V max.	I <sub>F</sub> = 30 mA
	Reverse current	I <sub>R</sub>	0.01 μA typ., 10 μA max.	V <sub>R</sub> = 4 V
	Peak emission wavelength	$\lambda_{P}$	940 nm typ.	I <sub>F</sub> = 20 mA
Detector	Light current	IL	50 μA min., 500 μA max.	$I_{\text{F}}$ = 20 mA, $V_{\text{CE}}$ = 10 V White paper with a reflection ratio of 90%, d = 3.5 mm (see note)
	Dark current	I <sub>D</sub>	2 nA typ., 200 nA max.	V <sub>CE</sub> = 10 V, 0 ℓx
	Leakage current	I <sub>LEAK</sub>	2 μA max.	I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 10 V with no reflection
	Collector–Emitter saturated voltage	V <sub>CE (sat)</sub>		
	Peak spectral sensitivity wavelength	$\lambda_{P}$	850 nm typ.	V <sub>CE</sub> = 10 V
Rising time	•	tr	30 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega, I_L = 1 \text{ mA}$
Falling time		tf	30 μs typ.	$V_{CC} = 5 \text{ V}, R_L = 1 \text{ k}\Omega, I_L = 1 \text{ mA}$

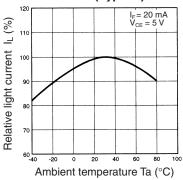
Note: The letter "d" indicates the distance between the top surface of the sensor and the sensing object.

### **■** Engineering Data

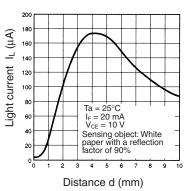
#### **Forward Current vs. Collector Dissipation Temperature Rating**



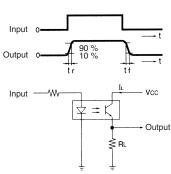
## Relative Light Current vs. Ambient Temperature Characteristics (Typical)



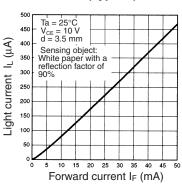
### **Sensing Distance Characteristics** (Typical)



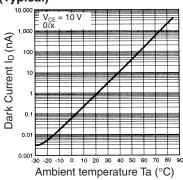
#### **Response Time Measurement** Circuit



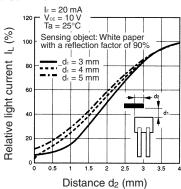
#### **Light Current vs. Forward Current Characteristics (Typical)**



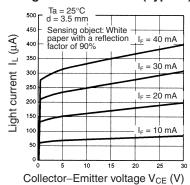
#### Dark Current vs. Ambient **Temperature Characteristics** (Typical)



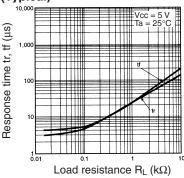
#### **Sensing Position Characteristics** (Typical)



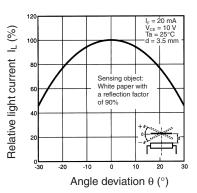
### Light Current vs. Collector-Emitter **Voltage Characteristics (Typical)**



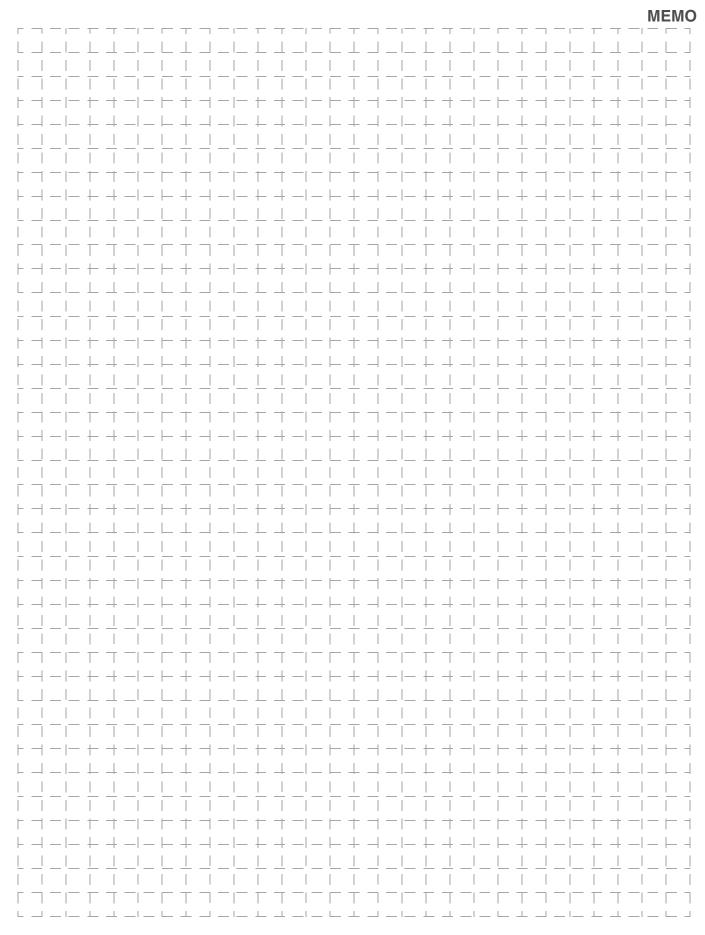
#### Response Time vs. Load **Resistance Characteristics** (Typical)



#### **Sensing Angle Characteristics** (Typical)









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